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August 2014

FGA30N65SMD 650 V, 30 A Field Stop IGBT

Features

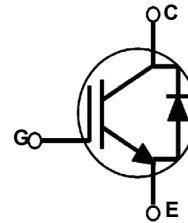
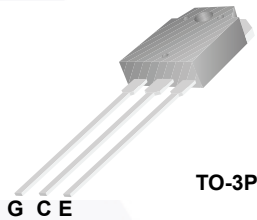
- Maximum Junction Temperature : $T_J = 175^\circ\text{C}$
- Positive Temperature Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)} = 1.98\text{ V(Typ.)} @ I_C = 30\text{ A}$
- High Input Impedance
- Fast Switching
- Tighten Parameter Distribution
- RoHS Compliant

Applications

- Solar Inverter
- UPS, Welder, SMPS

General Description

Using novel field stop IGBT technology, Fairchild's new series of field stop 2nd generation IGBTs offer the optimum performance for solar inverter, UPS, welder and PFC applications where low conduction and switching losses are essential.



Absolute Maximum Ratings

Symbol	Description	Ratings	Unit
V_{CES}	Collector to Emitter Voltage	650	V
V_{GES}	Gate to Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C = 25^\circ\text{C}$	60	A
	Collector Current @ $T_C = 100^\circ\text{C}$	30	A
$I_{CM(1)}$	Pulsed Collector Current	90	A
I_F	Diode Forward Current @ $T_C = 25^\circ\text{C}$	40	A
	Diode Forward Current @ $T_C = 100^\circ\text{C}$	20	A
$I_{FM(1)}$	Pulsed Diode Maximum Forward Current	120	A
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	300	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	150	W
T_J	Operating Junction Temperature	-55 to +175	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +175	$^\circ\text{C}$
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Notes:

1: Repetitive rating: Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Max.	Unit
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction to Case, Max.	0.5	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$ (Diode)	Thermal Resistance, Junction to Case, Max.	1.5	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	$^{\circ}\text{C}/\text{W}$

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGA30N65SMD	FGA30N65SMD	TO-3P	Tube	N/A	N/A	30

Electrical Characteristics of the IGBT $T_C = 25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{CES}	Collector to Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 250\ \mu\text{A}$	650	-	-	V
$\frac{\Delta BV_{CES}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 250\ \mu\text{A}$	-	0.29	-	$\text{V}/^{\circ}\text{C}$
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0\text{ V}$	-	-	250	μA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0\text{ V}$	-	-	± 400	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 250\ \mu\text{A}, V_{CE} = V_{GE}$	3.5	4.8	6.0	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 30\text{ A}, V_{GE} = 15\text{ V}$	-	1.98	2.5	V
		$I_C = 30\text{ A}, V_{GE} = 15\text{ V}, T_C = 175^{\circ}\text{C}$	-	2.29	-	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	-	1350	-	pF
C_{oes}	Output Capacitance		-	130	-	pF
C_{res}	Reverse Transfer Capacitance		-	45	-	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{ V}, I_C = 30\text{ A}, R_G = 6\ \Omega, V_{GE} = 15\text{ V}, \text{Inductive Load}, T_C = 25^{\circ}\text{C}$	-	14	-	ns
t_r	Rise Time		-	28	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	102	-	ns
t_f	Fall Time		-	10	-	ns
E_{on}	Turn-On Switching Loss		-	716	-	μJ
E_{off}	Turn-Off Switching Loss		-	208	-	μJ
E_{ts}	Total Switching Loss	-	924	-	μJ	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{ V}, I_C = 30\text{ A}, R_G = 6\ \Omega, V_{GE} = 15\text{ V}, \text{Inductive Load}, T_C = 175^{\circ}\text{C}$	-	13	-	ns
t_r	Rise Time		-	28	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	108	-	ns
t_f	Fall Time		-	17	-	ns
E_{on}	Turn-On Switching Loss		-	1125	-	μJ
E_{off}	Turn-Off Switching Loss		-	572	-	μJ
E_{ts}	Total Switching Loss		-	1697	-	μJ

Electrical Characteristics of the IGBT (Continued)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max	Unit
Q_g	Total Gate Charge	$V_{CE} = 400\text{ V}$, $I_C = 30\text{ A}$, $V_{GE} = 15\text{ V}$	-	87	-	nC
Q_{ge}	Gate to Emitter Charge		-	9.1	-	nC
Q_{gc}	Gate to Collector Charge		-	45	-	nC

Electrical Characteristics of the Diode $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max	Unit	
V_{FM}	Diode Forward Voltage	$I_F = 20\text{ A}$	$T_C = 25^\circ\text{C}$	-	2.1	2.7	V
			$T_C = 175^\circ\text{C}$	-	1.83	-	
E_{rec}	Reverse Recovery Energy	$I_F = 20\text{ A}$, $di_F/dt = 200\text{ A}/\mu\text{s}$	$T_C = 175^\circ\text{C}$	-	55	-	μJ
t_{rr}	Diode Reverse Recovery Time		$T_C = 25^\circ\text{C}$	-	35	-	ns
			$T_C = 175^\circ\text{C}$	-	182	-	
Q_{rr}	Diode Reverse Recovery Charge		$T_C = 25^\circ\text{C}$	-	59	-	nC
		$T_C = 175^\circ\text{C}$	-	587	-		



Typical Performance Characteristics

Figure 1. Typical Output Characteristics

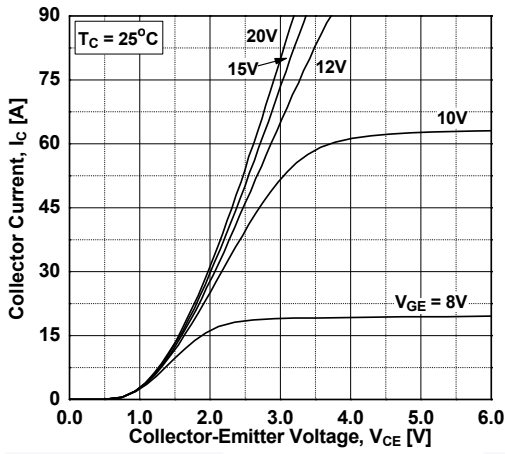


Figure 2. Typical Output Characteristics

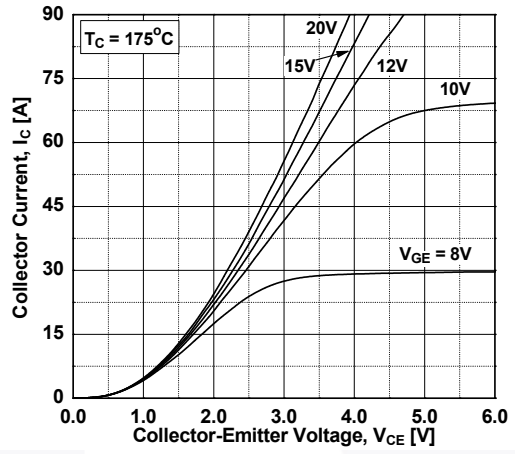


Figure 3. Typical Saturation Voltage Characteristics

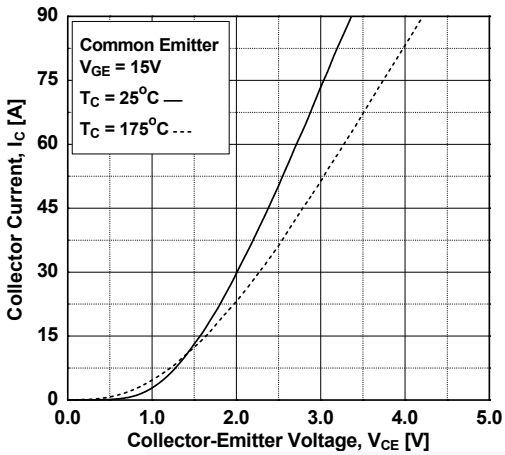


Figure 4. Saturation Voltage vs. Case Temperature at Variant Current Level

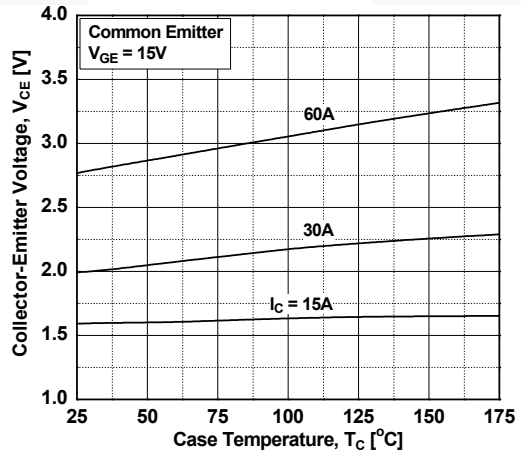


Figure 5. Saturation Voltage vs. Vge

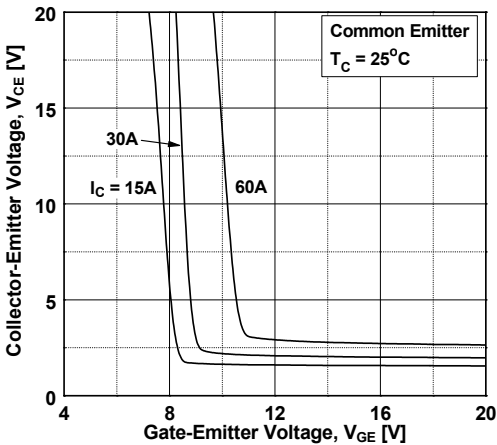
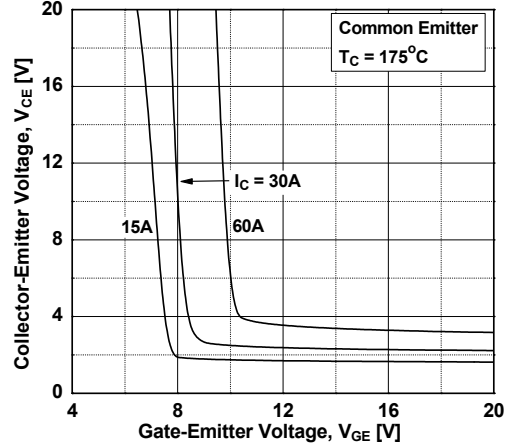


Figure 6. Saturation Voltage vs. Vge



Typical Performance Characteristics

Figure 7. Capacitance Characteristics

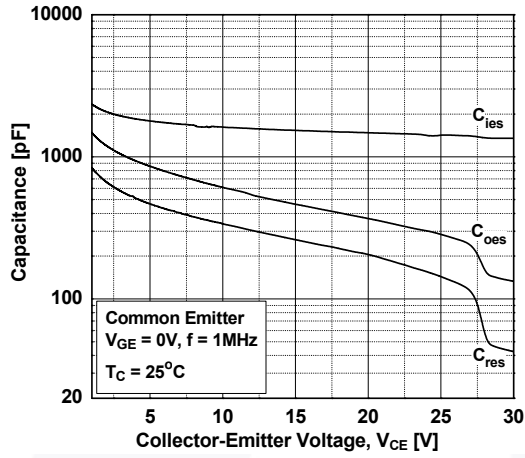


Figure 8. Gate charge Characteristics

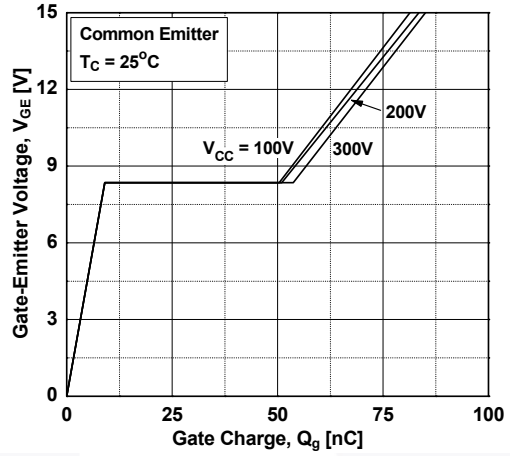


Figure 9. Turn-on Characteristics vs. Gate Resistance

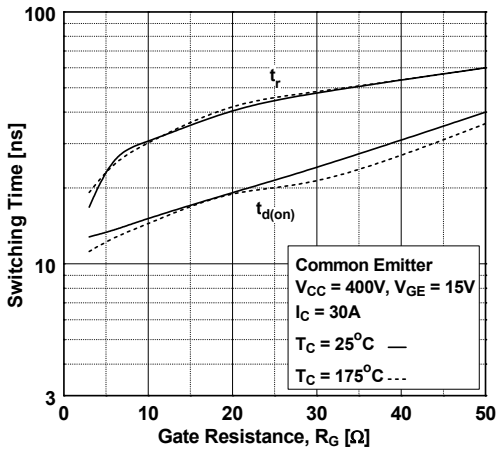


Figure 10. Turn-off Characteristics vs. Gate Resistance

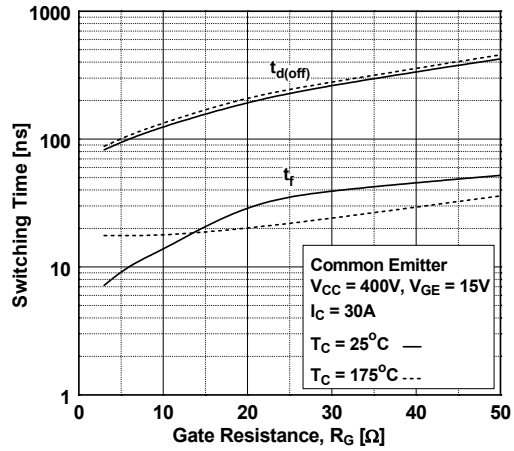


Figure 11. Switching Loss vs. Gate Resistance

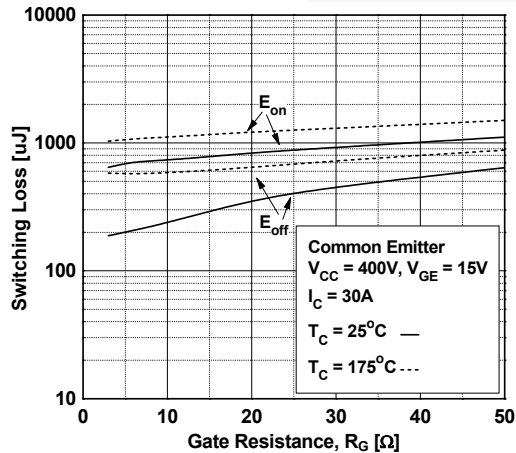
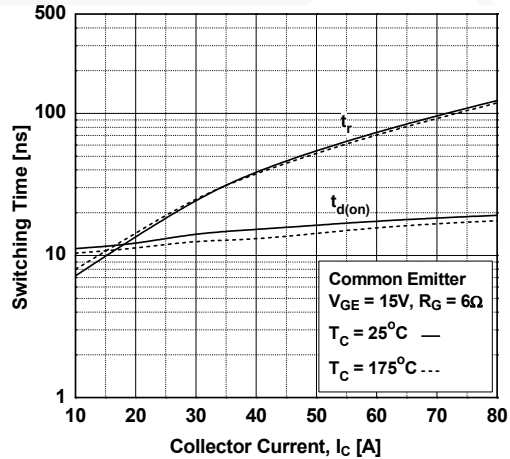


Figure 12. Turn-on Characteristics vs. Collector Current



Typical Performance Characteristics

Figure 13. Turn-off Characteristics vs. Collector Current

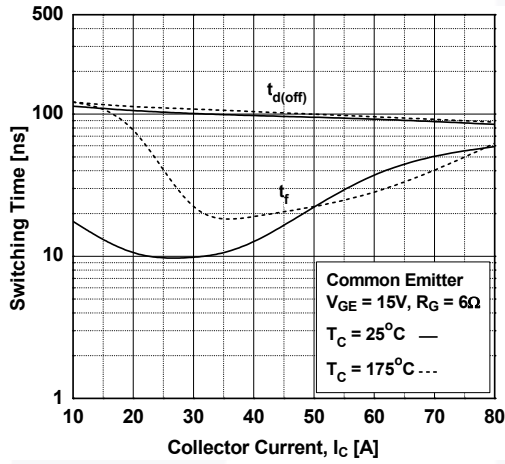


Figure 14. Switching Loss vs. Collector Current

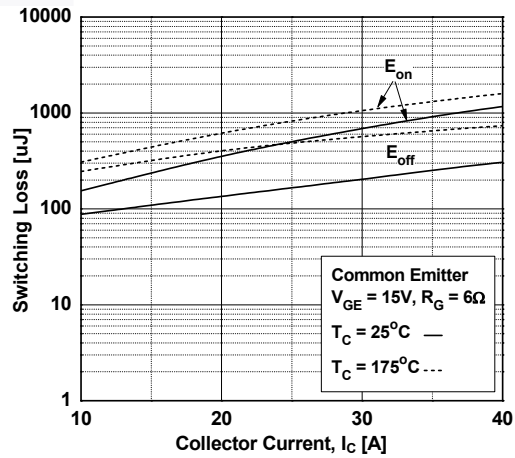


Figure 15. Load Current Vs. Frequency

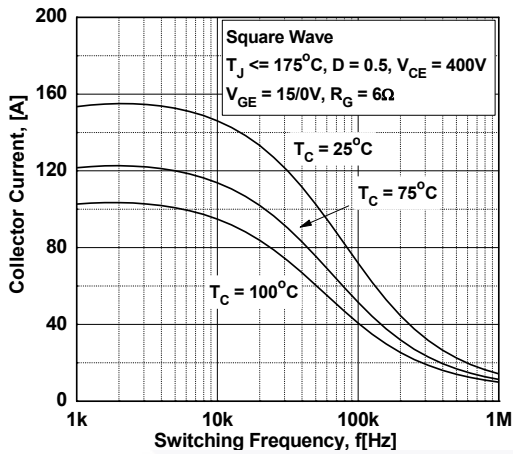


Figure 16. SOA Characteristics

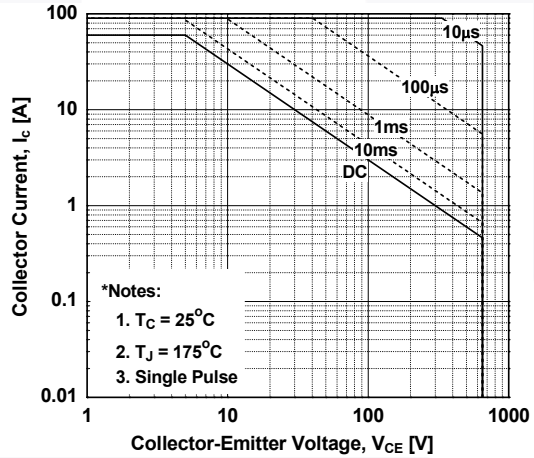


Figure 17. Forward Characteristics

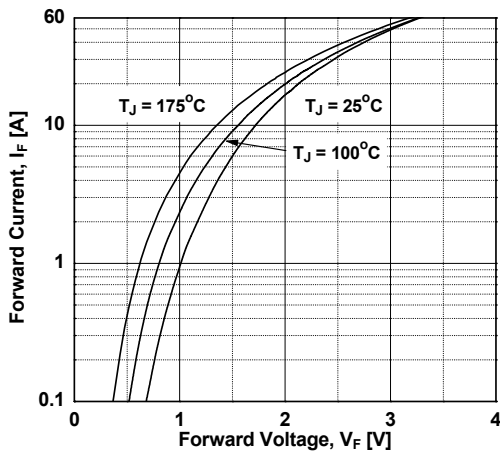
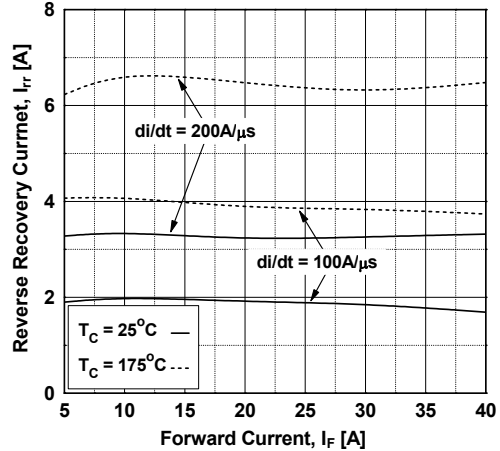


Figure 18. Reverse Recovery Current



Typical Performance Characteristics

Figure 19. Reverse Recovery Time

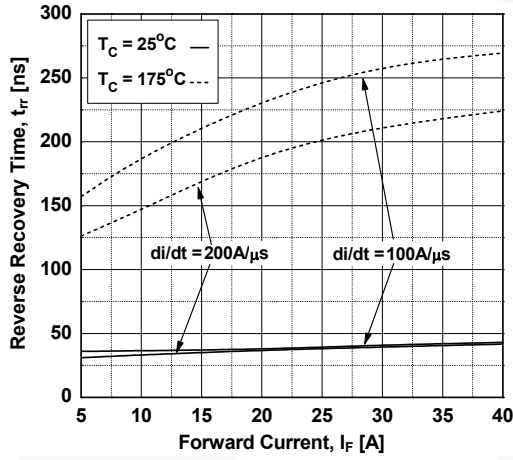


Figure 20. Stored Charge

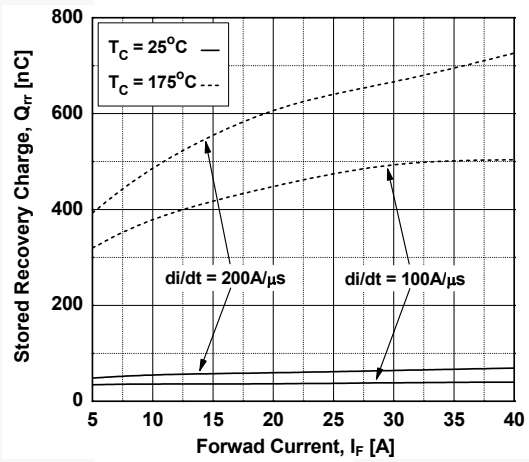


Figure 21. Transient Thermal Impedance of IGBT

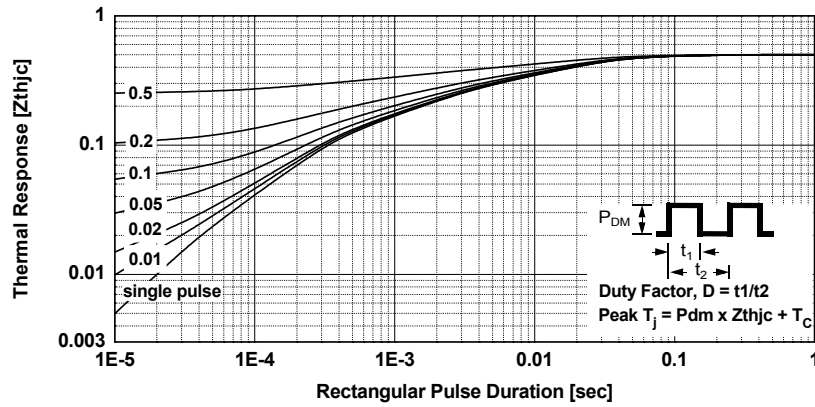
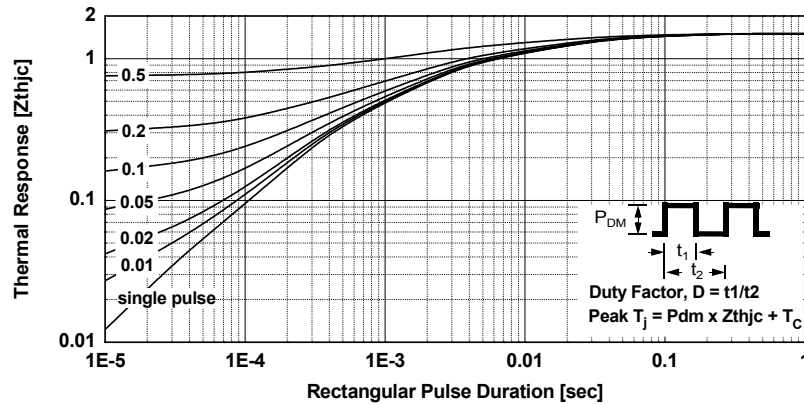
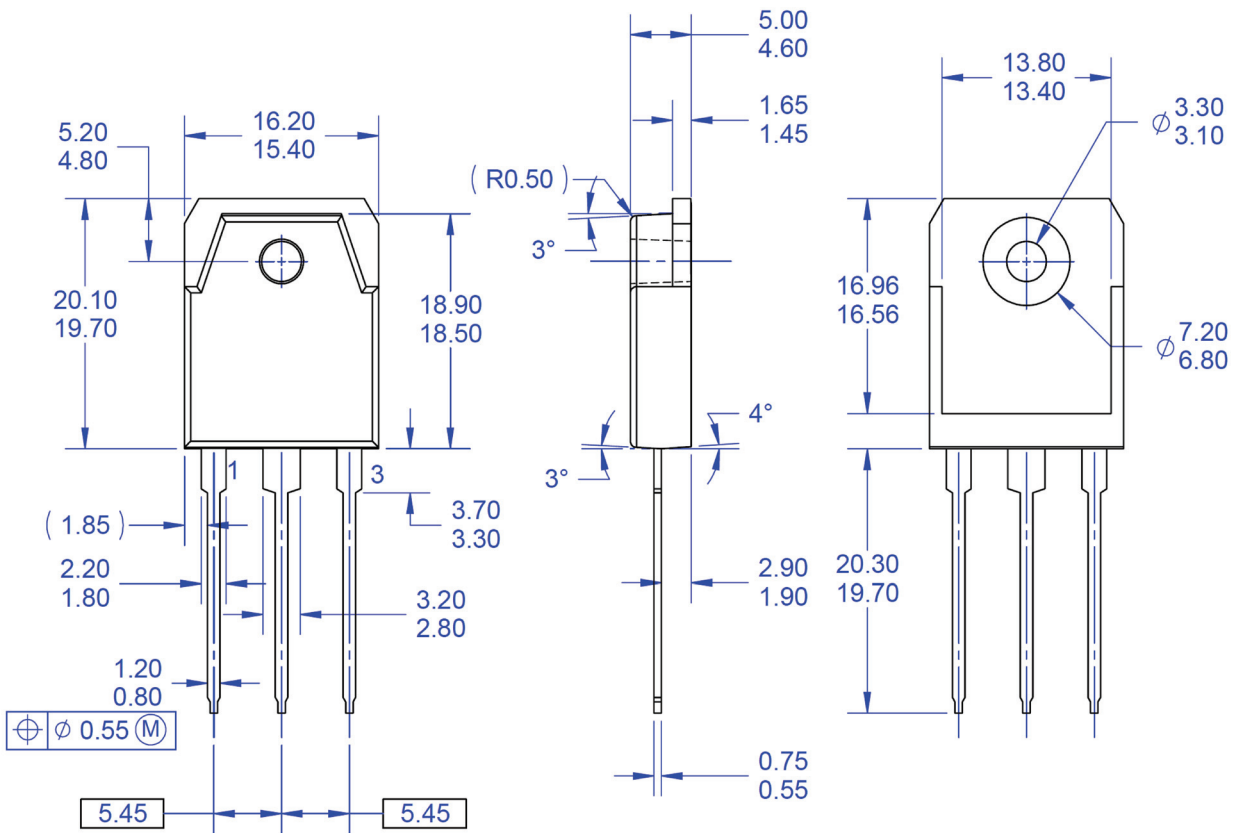


Figure 22. Transient Thermal Impedance of Diode



Mechanical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSION AND TOLERANCING PER ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- E) DRAWING FILE NAME: TO3PN03AREV1.
- F) FAIRCHILD SEMICONDUCTOR.

Figure 23. TO-3P 3L - 3LD, T03, PLASTIC, EIAJ SC-65

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No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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